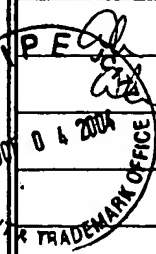



INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number 45114	ATTORNEY'S DKT No. H1494		APPLICATION No. 10/674,520	
			APPLICANT(S) Haihong Wang et al.			
			FILING DATE October 1, 2003		GROUP 2811	

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	4,399,605	08-23-83	Dash et al.	29	571	02-26-82
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FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

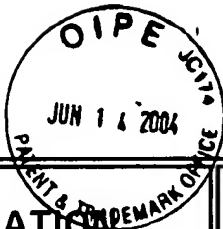
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	

EXAMINER 	DATE CONSIDERED 10/28/07
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number 26615	ATTORNEY'S DKT NO. H1494		APPLICATION No. Unassigned	
			APPLICANT(S) Haihong Wang et al.			
			FILING DATE October 1, 2003		GROUP Unassigned	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
Ah	Digh Hisamoto et al.: "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.					
Ah	Yang-Kyu Choi et al.: "Sub-20nm CMOS Fin FET Technologies," 2001 IEEE, IEDM, pages 421-424.					
Ah	Xuejue Huang et al.: "Sub-50 nm P-Channel Fin FET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.					
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Ah	Xuejue Huang et al.: "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.					
Ah	Co-pending U.S. Patent Application Serial No. 10/614,001, filed July 8, 2003, entitled: "Selective Silicidation of Gates in Semiconductor Devices to Achieve Multiple Threshold Voltages"; Shibly S. Ahmed et al.; 20 page specification, 8 sheets of drawings.					
EXAMINER <i>Andy Huang</i>				DATE CONSIDERED <i>10/28/04</i>		

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		CUSTOMER NUMBER 26615	ATTORNEY'S DKT No. H1494		APPLICATION No. 10/674,520		
			APPLICANT(S) Haihong WANG et al.				
			FILING DATE October 1, 2003		GROUP 2811		
U.S. PATENT DOCUMENTS							
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ah	6,391,750 B1	05/21/2002	Chen et al.	438	583		
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ah	US 2004/0048424 A1	03/11/2004	Wu et al.	438	154		
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
ah	Copy of co-pending U.S. Patent Application No. 10/857,931; by Haihong Wang et al.; filed June 2, 2004; 21 page specification; 20 sheets of drawings.						
EXAMINER			DATE CONSIDERED				
Andrew Kuy			10/28/04				

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